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(54) Title: VERTICAL METAL OXIDE SEMICONDUCTOR FIELD-EFFECT DIODES

(57) Abstract: The semiconductor diodes are diode configured vertical metal oxide semiconductor field effect devices formed using semiconductor pedestals (304) and having one diode terminal (324) as the common connection between the gates (318) and drains (312) of the vertical metal oxide semiconductor field effect devices, and one diode terminal (330) as the common connection with the sources (314) of the vertical metal oxide semiconductor field effect devices. Methods of manufacturing the vertical metal oxide seminconductor field effect devices are also disclosed.